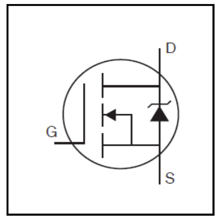
AUTOMOTIVE GRADE

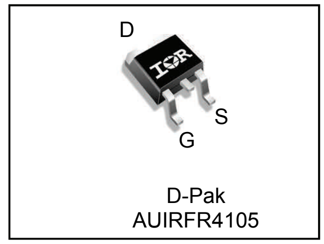
AUIRFR4105

HEXFET® Power MOSFET

Features
- Advanced Planar Technology
- Low On-Resistance
- Dynamic dV/dT Rating
- 175°C Operating Temperature
- Fast Switching
- Fully Avalanche Rated
- Repetitive Avalanche Allowed up to Tjmax
- Lead-Free, RoHS Compliant
- Automotive Qualified *



V_{DSS}		55V
$R_{DS(on)}$	max.	45mΩ
I_D (Silicon Limited)		27A⑤
I_D (Package Limited)		20A



D-Pak
AUIRFR4105

G	D	S
Gate	Drain	Source

Description
Specifically designed for Automotive applications, this cellular design of HEXFET® Power MOSFETs utilizes the latest processing techniques to achieve low on-resistance per silicon area. This benefit combined with the fast switching speed and ruggedized device design that HEXFET power MOSFETs are well known for, provides the designer with an extremely efficient and reliable device for use in Automotive and a wide variety of other applications.

Base part number	Package Type	Standard Pack		Orderable Part Number
		Form	Quantity	
AUIRFR4105	D-Pak	Tube	75	AUIRFR4105
		Tape and Reel Left	3000	AUIRFR4105TRL

Absolute Maximum Ratings
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only; and functional operation of the device at these or any other condition beyond those indicated in the specifications is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability. The thermal resistance and power dissipation ratings are measured under board mounted and still air conditions. Ambient temperature (TA) is 25°C, unless otherwise specified.

Symbol	Parameter	Max.	Units
I_D @ T_C = 25°C	Continuous Drain Current, V_{GS} @ 10V (Silicon Limited)	27⑤	A
I_D @ T_C = 100°C	Continuous Drain Current, V_{GS} @ 10V (Silicon Limited)	19	
I_D @ T_C = 25°C	Continuous Drain Current, V_{GS} @ 10V (Package Limited)	20	
I_{DM}	Pulsed Drain Current ①	100	
P_D @T_C = 25°C	Maximum Power Dissipation	68	W
	Linear Derating Factor	0.45	W/°C
V_{GS}	Gate-to-Source Voltage	± 20	V
E_{AS}	Single Pulse Avalanche Energy (Thermally Limited) ②	65	mJ
E_{AS} (Tested)	Single Pulse Avalanche Energy Tested Value ⑥	16	
I_{AR}	Avalanche Current ①	6.8	A
E_{AR}	Repetitive Avalanche Energy ⑤	5.0	mJ
T_J T_{STG}	Operating Junction and Storage Temperature Range	-55 to + 175	°C
	Soldering Temperature, for 10 seconds (1.6mm from case)	300	

Thermal Resistance

Symbol	Parameter	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case ⑥	——	2.2	°C/W
$R_{\theta JA}$	Junction-to-Ambient (PCB Mount) ⑦	——	50	
$R_{\theta JA}$	Junction-to-Ambient	——	110	

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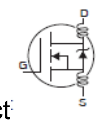
*Qualification standards can be found at www.infineon.com

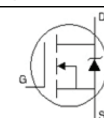
Static @ T_J = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	55	——	——	V	V_{GS} = 0V, I_D = 250μA
$\Delta V_{(BR)DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	——	0.052	——	V/°C	Reference to 25°C, I_D = 1mA
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	——	——	45	mΩ	V_{GS} = 10V, I_D = 16A ④
$V_{GS(th)}$	Gate Threshold Voltage	2.0	——	4.0	V	V_{DS} = V_{GS}, I_D = 250μA
gfs	Forward Trans conductance	6.5	——	——	S	V_{DS} = 25V, I_D = 16A ④
I_{DSS}	Drain-to-Source Leakage Current	——	——	25	μA	V_{DS} = 55V, V_{GS} = 0V
		——	——	250		V_{DS} = 44V,V_{GS} = 0V,T_J =150°C
I_{GSS}	Gate-to-Source Forward Leakage	——	——	100	nA	V_{GS} = 20V
	Gate-to-Source Reverse Leakage	——	——	-100		V_{GS} = -20V

Dynamic Electrical Characteristics @ T_J = 25°C (unless otherwise specified)

Q_g	Total Gate Charge	——	——	34	nC	I_D = 16A
Q_{gs}	Gate-to-Source Charge	——	——	6.8		V_{DS} = 44V
Q_{gd}	Gate-to-Drain Charge	——	——	14		V_{GS} = 10V, See Fig. 6 &13 ④
$t_{d(on)}$	Turn-On Delay Time	——	7.0	——	ns	V_{DD} = 28V
t_r	Rise Time	——	49	——		I_D = 16A
$t_{d(off)}$	Turn-Off Delay Time	——	31	——		R_G = 18Ω
t_f	Fall Time	——	40	——		R_D = 1.8Ω,See Fig. 10④
L_D	Internal Drain Inductance	——	4.5	——	nH	Between lead, 6mm (0.25in.) from package and center of die contact 
L_S	Internal Source Inductance	——	7.5	——		
C_{iss}	Input Capacitance	——	700	——	pF	V_{GS} = 0V
C_{oss}	Output Capacitance	——	240	——		V_{DS} = 25V
C_{rss}	Reverse Transfer Capacitance	——	100	——		f = 1.0MHz, See Fig.5

Diode Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
I_S	Continuous Source Current (Body Diode)	——	——	27⑤	A	MOSFET symbol showing the integral reverse p-n junction diode. 
I_{SM}	Pulsed Source Current (Body Diode) ①	——	——	100		
V_{SD}	Diode Forward Voltage	——	——	1.6	V	T_J = 25°C,I_S = 16A, V_{GS} = 0V ④
t_{rr}	Reverse Recovery Time	——	57	86	ns	T_J = 25°C ,I_F = 16A
Q_{rr}	Reverse Recovery Charge	——	130	200	nC	di/dt = 100A/μs④
t_{on}	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by L_S+L_D)				

Notes:

① Repetitive rating; pulse width limited by max. junction temperature. (See fig. 11)
② V_{DD} = 25V, , starting T_J = 25°C, L = 410μH, R_G = 25Ω, I_{AS} = 16A, V_{GS} =10V. (See fig. 12)
③ $I_{SD} \leq$ 16A, di/dt $\leq$ 420A/μs, $V_{DD} \leq V_{(BR)DSS}$, $T_J \leq$ 175°C.
④ Pulse width $\leq$ 300μs; duty cycle $\leq$ 2%.
⑤ Calculated continuous current based on maximum allowable junction temperature. Package limitation current is 20A.
⑤ Limited by T_{Jmax} , see Fig.12a, 12b, 15, 16 for typical repetitive avalanche performance.
⑥ R_θ is measured at T_J approximately 90°C.
⑦ When mounted on 1" square PCB (FR-4 or G-10 Material). For recommended footprint and soldering techniques refer to application note #AN-994

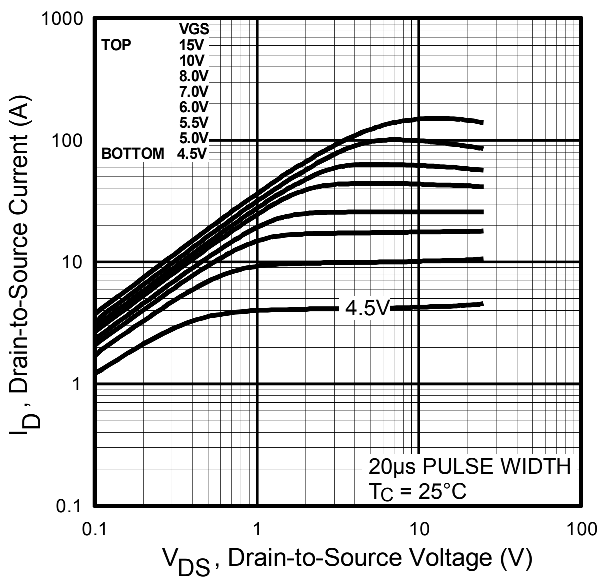


Fig. 1 Typical Output Characteristics

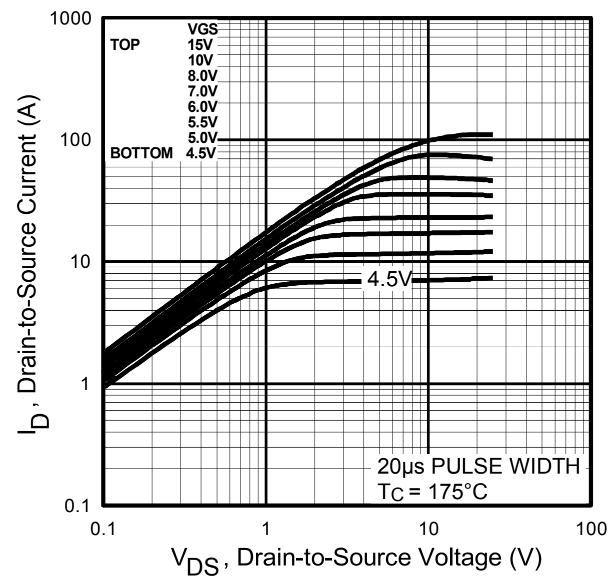


Fig. 2 Typical Output Characteristics

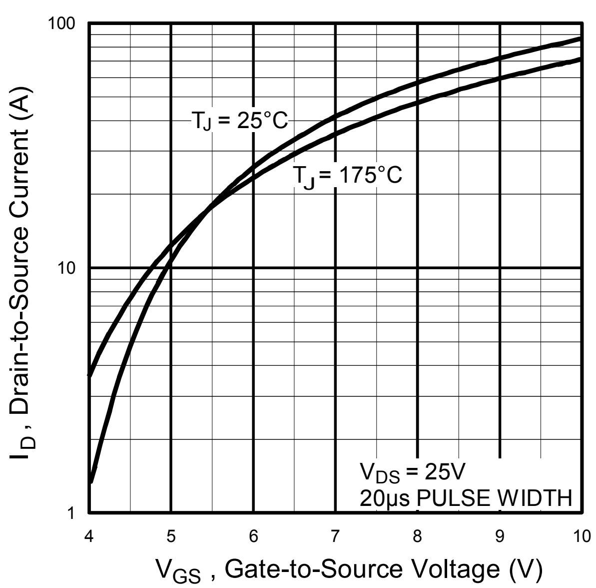


Fig. 3 Typical Transfer Characteristics

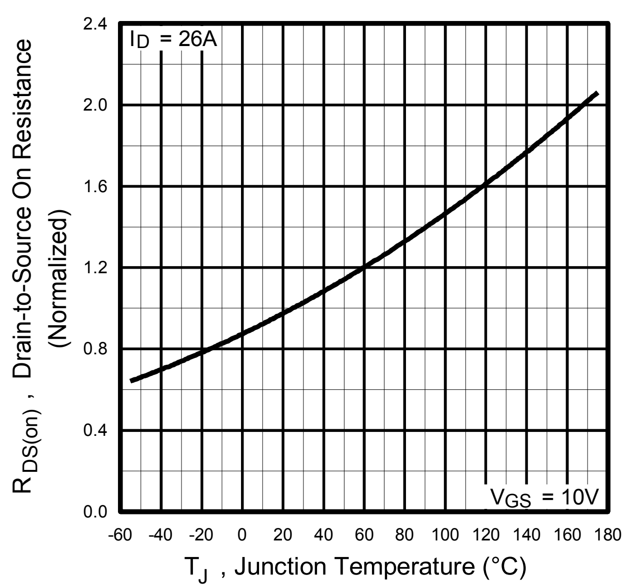


Fig. 4 Normalized On-Resistance Vs. Temperature

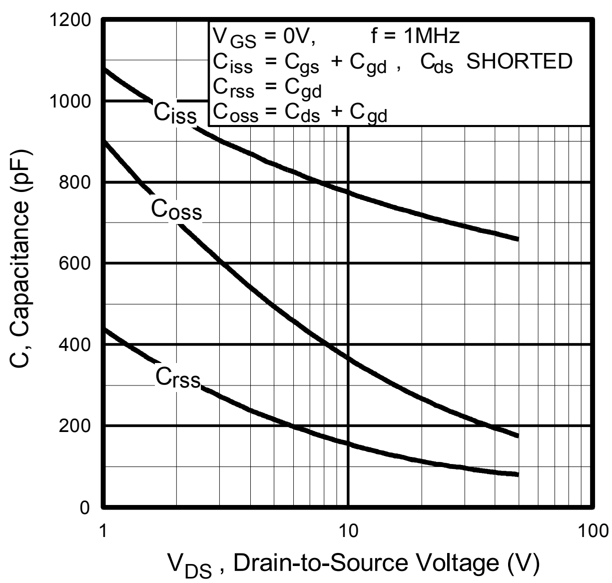


Fig 5. Typical Capacitance vs. Drain-to-Source Voltage

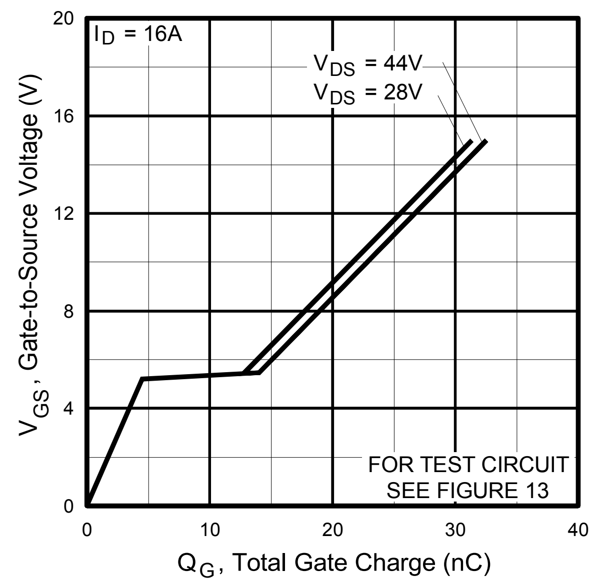


Fig 6. Typical Gate Charge vs. Gate-to-Source Voltage

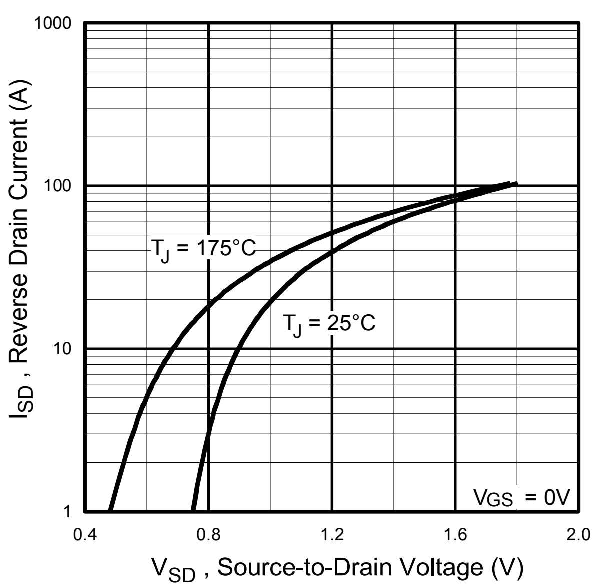


Fig. 7 Typical Source-to-Drain Diode Forward Voltage

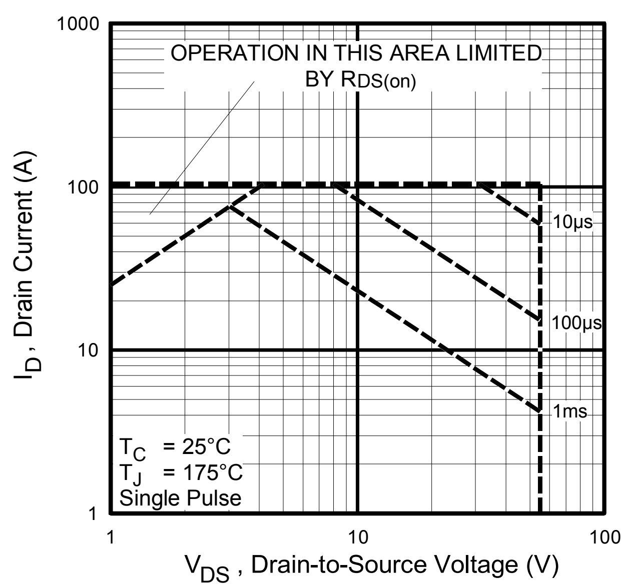


Fig 8. Maximum Safe Operating Area

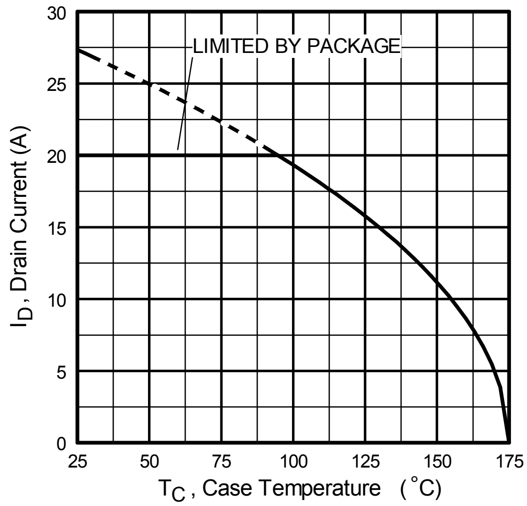


Fig 9. Maximum Drain Current Vs. Case Temperature

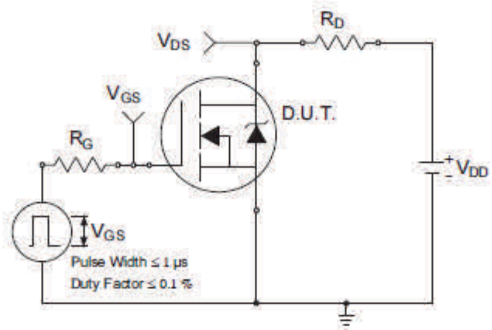


Fig 10a. Switching Time Test Circuit

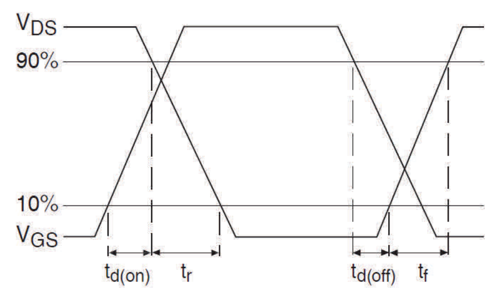


Fig 10b. Switching Time Waveforms

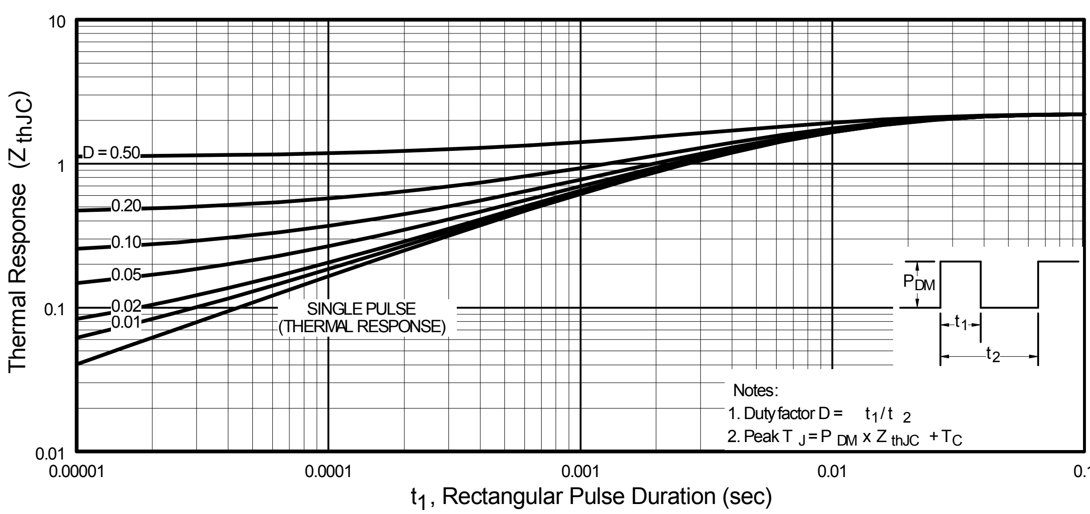


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Case

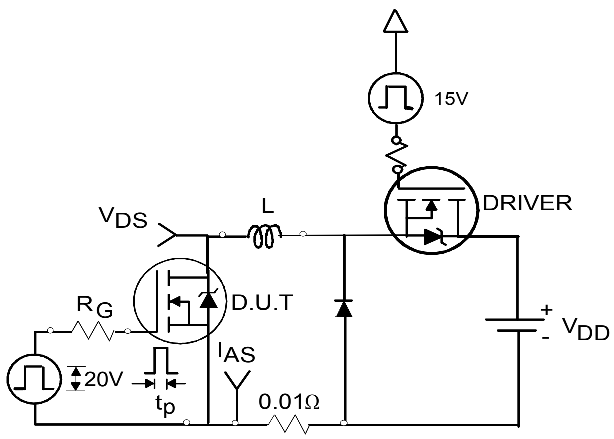


Fig 12a. Unclamped Inductive Test Circuit

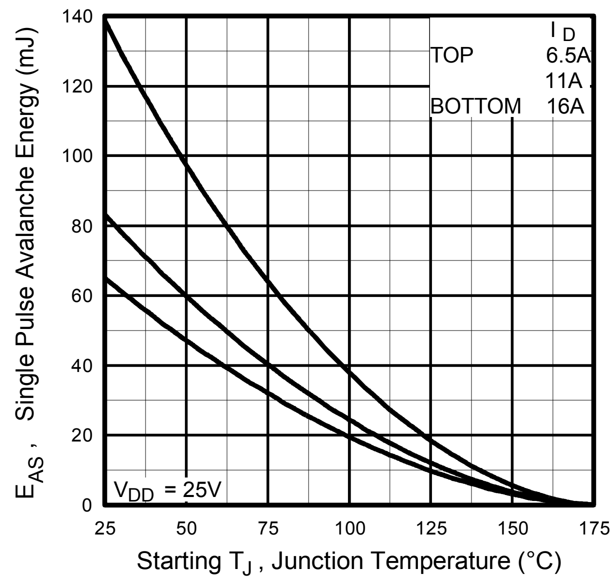


Fig 12c. Maximum Avalanche Energy vs. Drain Current

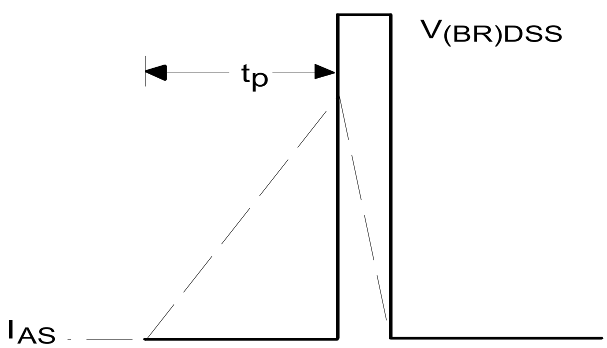


Fig 12b. Unclamped Inductive Waveforms

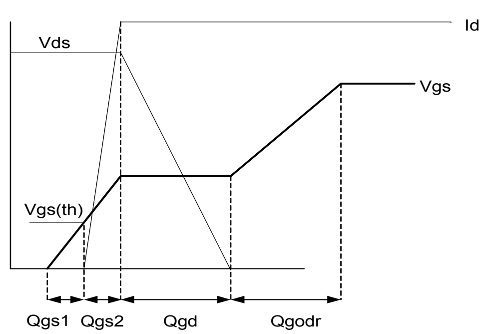


Fig 13a. Gate Charge Waveform

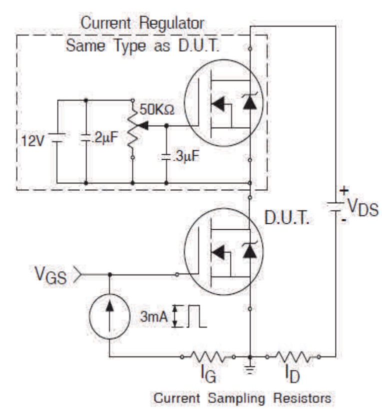
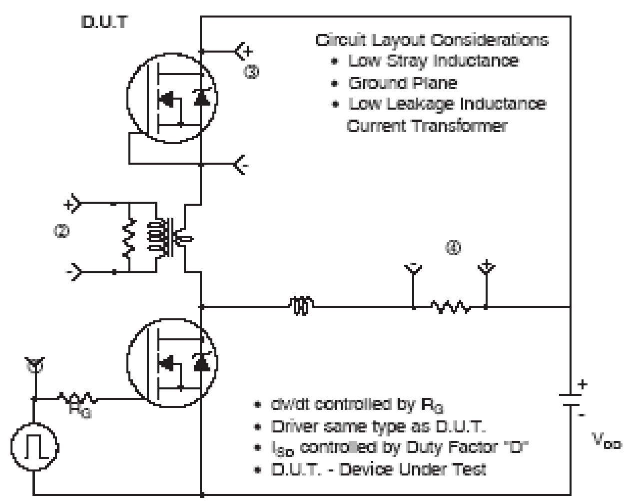
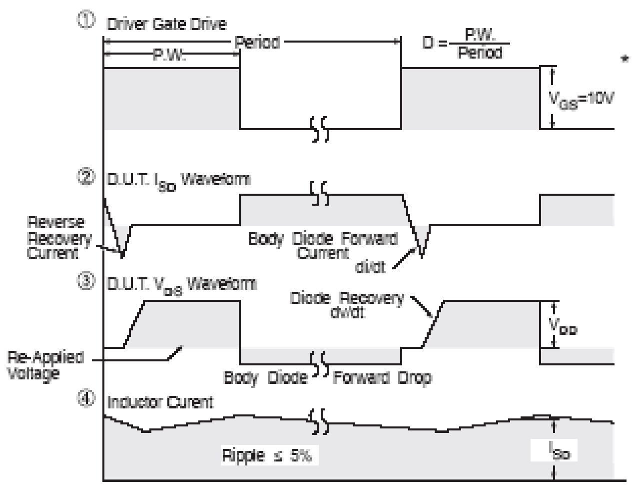


Fig 13b. Gate Charge Test Circuit

Peak Diode Recovery dv/dt Test Circuit

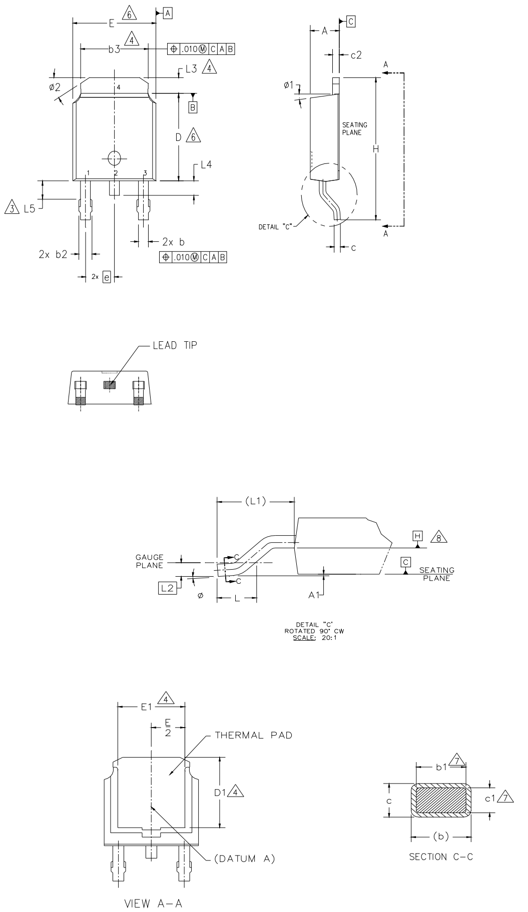




* V_{GS} = 5V for Logic Level Devices

Fig 14. Peak Diode Recovery dv/dt Test Circuit for N-Channel HEXFET® Power MOSFETs

D-Pak (TO-252AA) Package Outline (Dimensions are shown in millimeters (inches))



NOTES:

1.– DIMENSIONING AND TOLERANCING PER ASME Y14.5M–1994
2.– DIMENSION ARE SHOWN IN INCHES [MILLIMETERS].
3.– LEAD DIMENSION UNCONTROLLED IN L5.
4.– DIMENSION D1, E1, L3 & b3 ESTABLISH A MINIMUM MOUNTING SURFACE FOR THERMAL PAD.
5.– SECTION C–C DIMENSIONS APPLY TO THE FLAT SECTION OF THE LEAD BETWEEN .005 AND 0.10 [0.13 AND 0.25] FROM THE LEAD TIP.
6.– DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED .005 [0.13] PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTMOST EXTREMES OF THE PLASTIC BODY.
7.– DIMENSION b1 & c1 APPLIED TO BASE METAL ONLY.
8.– DATUM A & B TO BE DETERMINED AT DATUM PLANE H.
9.– OUTLINE CONFORMS TO JEDEC OUTLINE TO-252AA.

SYMBOL	DIMENSIONS				NOTES
	MILLIMETERS		INCHES		
	MIN.	MAX.	MIN.	MAX.	
A	2.18	2.39	.086	.094	
A1	–	0.13	–	.005	
b	0.64	0.89	.025	.035	
b1	0.65	0.79	.025	.031	7
b2	0.76	1.14	.030	.045	
b3	4.95	5.46	.195	.215	4
c	0.46	0.61	.018	.024	
c1	0.41	0.56	.016	.022	7
c2	0.46	0.89	.018	.035	
D	5.97	6.22	.235	.245	6
D1	5.21	–	.205	–	4
E	6.35	6.73	.250	.265	6
E1	4.32	–	.170	–	4
e	2.29 BSC		.090 BSC		
H	9.40	10.41	.370	.410	
L	1.40	1.78	.055	.070	
L1	2.74 BSC		.108 REF.		
L2	0.51 BSC		.020 BSC		
L3	0.89	1.27	.035	.050	4
L4	–	1.02	–	.040	
L5	1.14	1.52	.045	.060	3
ø	0°	10°	0°	10°	
ø1	0°	15°	0°	15°	
ø2	25°	35°	25°	35°	

LEAD ASSIGNMENTS

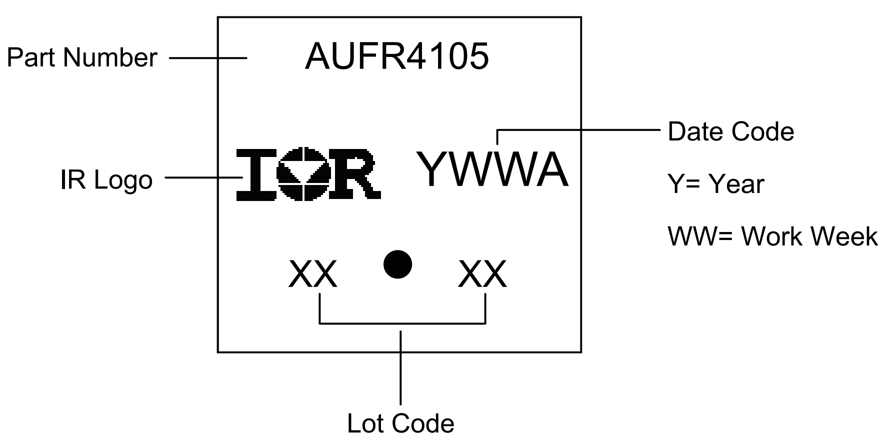
HEXFET

1.– GATE
2.– DRAIN
3.– SOURCE
4.– DRAIN

IGBT & CoPAK

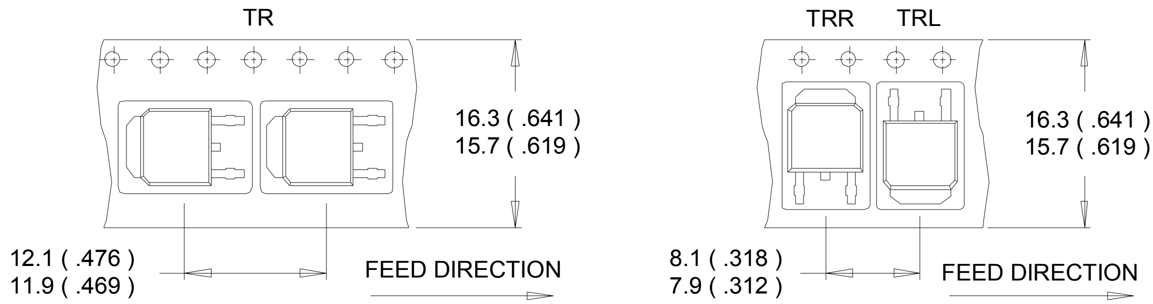
1.– GATE
2.– COLLECTOR
3.– EMITTER
4.– COLLECTOR

D-Pak (TO-252AA) Part Marking Information

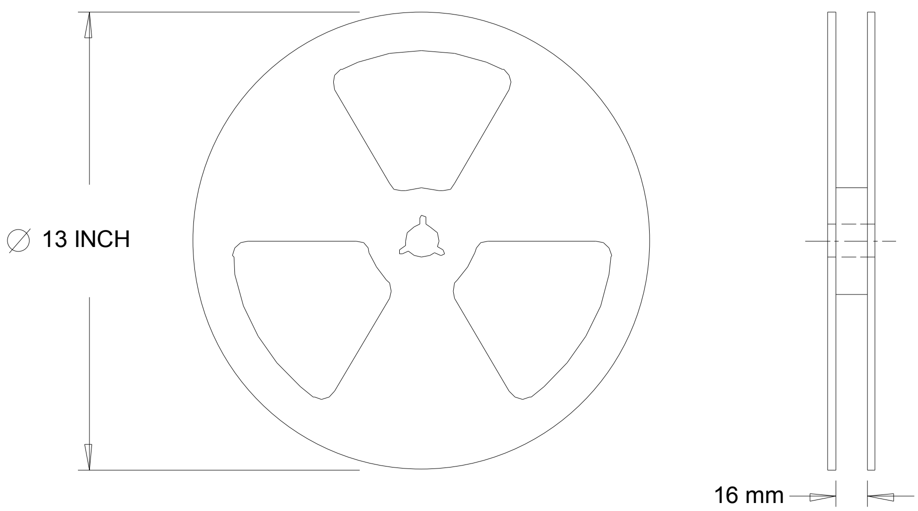


Note: For the most current drawing please refer to IR website at http://www.irf.com/package/

D-Pak (TO-252AA) Tape & Reel Information (Dimensions are shown in millimeters (inches))



NOTES :
1. CONTROLLING DIMENSION : MILLIMETER.
2. ALL DIMENSIONS ARE SHOWN IN MILLIMETERS (INCHES).
3. OUTLINE CONFORMS TO EIA-481 & EIA-541.



NOTES :
1. OUTLINE CONFORMS TO EIA-481.

Note: For the most current drawing please refer to IR website at http://www.irf.com/package/

Qualification Information

Qualification Level		Automotive (per AEC-Q101)	
		Comments: This part number(s) passed Automotive qualification. Infineon's Industrial and Consumer qualification level is granted by extension of the higher Automotive level.	
Moisture Sensitivity Level		D-Pak	MSL1
ESD	Machine Model	Class M2 (+/- 200V)† AEC-Q101-002	
	Human Body Model	Class H1B (+/- 900V) † AEC-Q101-001	
	Charged Device Model	Class C5 (+/- 1125V)† AEC-Q101-005	
RoHS Compliant		Yes	

† Highest passing voltage.

Revision History

Date	Comments
12/1/2015	• Updated datasheet with corporate template • Corrected ordering table on page 1.

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